

FSB67508

Smart Power Module (SPM®)

Features

- $R_{DS(ON),MAX}=11m\Omega$ @ $I_D=38A, T_J=25^\circ C$ a half-bridge FRFET inverter including high voltage integrated circuit (HVIC)
- Negative dc-link terminals for inverter current sensing applications
- HVIC for gate driving and protection functions
- 3/5V CMOS/TTL compatible, active-high interface
- Isolation voltage rating of 1500Vrms for 1min.
- Embedded bootstrap diode in the package

General Description

FSB67508 is a smart power module (SPM®) as a compact solution for small power motor drive applications such as E-bike. It is composed of 2 MOSFET, and 1 half-bridge HVIC for gate driving. This offers an extremely compact, high performance half-bridge inverter in a single isolated package. The package is optimized for the thermal performance and compactness for the use in the built-in motor application and any other application where the assembly space is concerned.



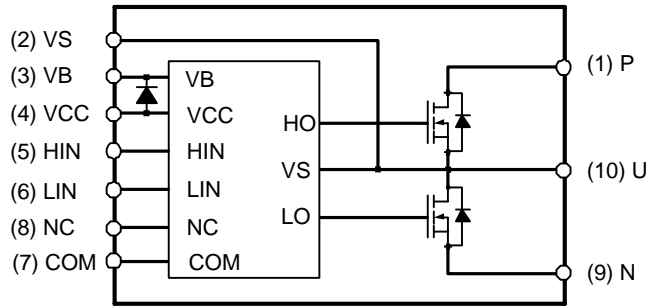
Absolute Maximum Ratings

Symbol	Parameter	Conditions	Rating	Units
V_{PN}	DC Link Input Voltage, Drain-source Voltage of each FET		75	V
I_{D25}	Each FET Drain Current, Continuous	$T_C = 25^\circ C$	38	A
I_{D80}	Each FET Drain Current, Continuous	$T_C = 80^\circ C$	28	A
I_{DP}	Each FET Drain Current, Peak	$T_C = 25^\circ C$, Pulsed*	95	A
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$, Each	32	W
V_{CC}	Control Supply Voltage	Applied between V_{CC} and COM	20	V
V_{BS}	High-side Bias Voltage	Applied between V_B and U	20	V
V_{IN}	Input Signal Voltage	Applied between IN and COM	-0.3 ~ V_{CC}	V
T_J	Operating Junction Temperature		-40 ~ 150	$^\circ C$
T_{STG}	Storage Temperature		-50 ~ 150	$^\circ C$
$R_{\theta JC}$	Junction to Case Thermal Resistance	Each under inverter operating condition (Note 1)	3.9	$^\circ C/W$

*Repetitive rating : Pulse width limited by maximum junction temperature

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	P	Positive DC-Link Input
2	VS	Bias Voltage Ground for High Side MOSFET Driving
3	VB	High-side Bias Voltage for MOSFET Driving
4	VCC	Bias Voltage for IC and Low side MOSFET Driving
5	HIN	Signal Input for High-side
6	LIN	Signal Input for Low-side
7	COM	Common Supply Ground
8	NC	No connection
9	N	Negative DC-Link Input
10	U	Output



Note:

Source terminal of each low-side MOSFET is not connected to supply ground or bias voltage ground inside SPM®. External connections should be made as indicated in Figure2.

Figure 1. Internal Block Diagram

Electrical Characteristics (T_J = 25°C, V_{CC}=V_{BS}=15V Unless Otherwise Specified)

Inverter Part (Each MOSFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{IN} = 0V, I _D = 250μA (Note 2)	75	-	-	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.6	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{IN} = 0V, V _{DS} = 75V	-	-	250	μA
R _{DS(on)}	Static Drain-Source On-Resistance	V _{CC} = V _{BS} = 15V, V _{IN} = 5V, I _D = 15A	-	9.4	11	mΩ
V _{SD}	Drain-Source Diode Forward Voltage	V _{CC} = V _{BS} = 15V, V _{IN} = 0V, I _D = 15A	-	-	1.2	V
t _{ON}	Switching Times	V _{PN} = 48V, V _{CC} = V _{BS} = 15V, I _D = 15A V _{IN} = 0V ↔ 5V Inductive load L=3mH High- and low-side FET switching (Note 3)	-	550	-	ns
t _{OFF}			-	2000	-	ns
t _{rr}			-	100	-	ns
E _{ON}			-	40	-	μJ
E _{OFF}			-	190	-	μJ
RBSOA	Reverse-bias Safe Operating Area	V _{PN} = 55V, V _{CC} = V _{BS} = 15V, I _D = I _{DP} , V _{DS} =BV _{DSS} , T _J = 150°C High- and low-side FET switching (Note 3)	Full Square			

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I _{QCC}	Quiescent V _{CC} Current	V _{CC} =15V, V _{IN} =0V Applied between V _{CC} and COM	-	-	160	μA
I _{QBS}	Quiescent V _{BS} Current	V _{BS} =15V, V _{IN} =0V Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	-	-	100	μA
UV _{CCD}	Low-side Undervoltage Protection (Figure 6)	V _{CC} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV _{CCR}		V _{CC} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
UV _{BSD}	High-side Undervoltage Protection (Figure 7)	V _{BS} Undervoltage Protection Detection Level	7.4	8.0	9.4	V
UV _{BSR}		V _{BS} Undervoltage Protection Reset Level	8.0	8.9	9.8	V
V _{IH}	ON Threshold Voltage	Logic High Level	3.0	-	-	V
V _{IL}	OFF Threshold Voltage	Logic Low Level				
I _{IH}	Input Bias Current	V _{IN} = 5V	-	10	20	μA
I _{IL}		V _{IN} = 0V	-	-	2	μA

Note:

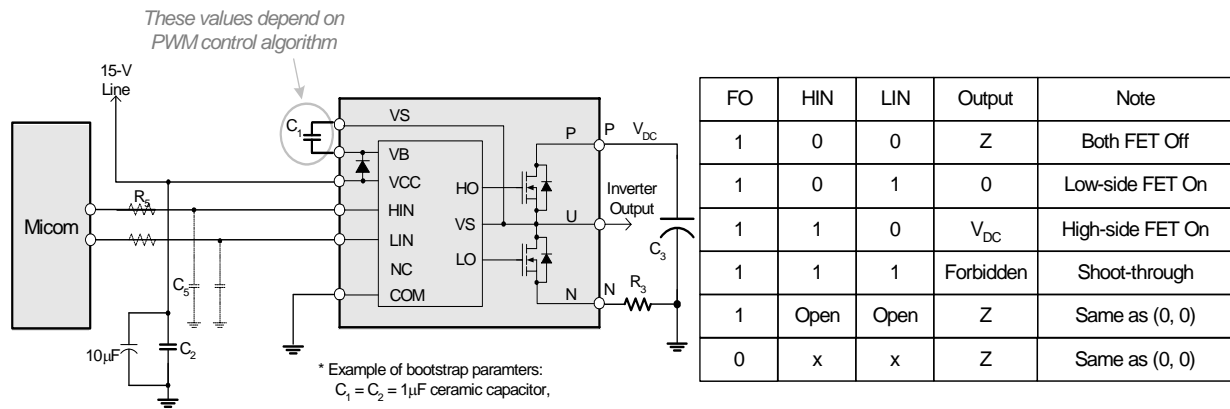
- BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each FET inside SPM®. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{DS} should not exceed BV_{DSS} in any case.
- t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 3 for the switching time definition with the switching test circuit of Figure 4.
- The peak current and voltage of each FET during the switching operation should be included in the safe operating area (SOA). Please see Figure 4 for the RBSOA test circuit that is same as the switching test circuit.

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FSB67508	FSB67508	SPM10-AA	-	-	19

Recommended Operating Conditions

Symbol	Parameter	Conditions	Value			Units
			Min.	Typ.	Max.	
V_{PN}	Supply Voltage	Applied between P and N	-	48	60	V
V_{CC}	Control Supply Voltage	Applied between V_{CC} and COM	13.5	15	16.5	V
V_{BS}	High-side Bias Voltage	Applied between V_B and output	13	15	16.5	V
$V_{IN(ON)}$	Input ON Threshold Voltage	Applied between IN and COM	3.0	-	V_{CC}	V
$V_{IN(OFF)}$	Input OFF Threshold Voltage		0	-	0.6	V
t_{dead}	Blanking Time for Preventing Arm-short	$V_{CC}=V_{BS}=13.5 \sim 20V, T_J \leq 150^\circ C$	1.0	-	-	μs
f_{PWM}	PWM Switching Frequency	$T_J \leq 150^\circ C$	-	15	-	kHz



Note:

- (1) The snubber capacitor, C_3 , should be placed near SPM®
- (2) Parameters for bootstrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- (3) RC coupling (R_5 and C_5) at each input (indicated as dotted lines) may be used to prevent improper input signal due to surge noise. Signal input of SPM® is compatible with standard CMOS or LSTTL output.
- (4) Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge voltage. Bypass capacitors such as C_1 , C_2 and C_3 should have good high-frequency characteristics to absorb high-frequency ripple current.

Figure 2. Recommended CPU Interface and Bootstrap Circuit with Parameters

Bootstrap Diode Part

Symbol	Parameter	Conditions	Rating	Units
V_{RRM}	Maximum Repetitive Reverse Voltage		75	V
I_F	Forward Current	$T_C = 25^\circ C$	0.5	A
I_{FP}	Forward Current (Peak)	$T_C = 25^\circ C$, Under 1ms Pulse Width	2	A
T_J	Operating Junction Temperature		-40 ~ 150	$^\circ C$
R_B	Equivalent Bootstrap Resistance	$T_C = 25^\circ C$	15	Ω

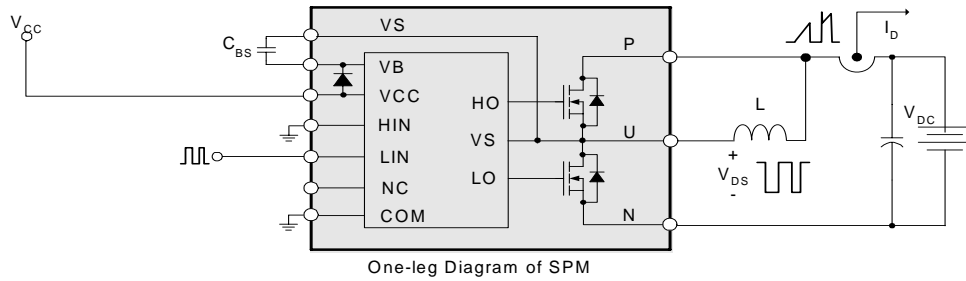
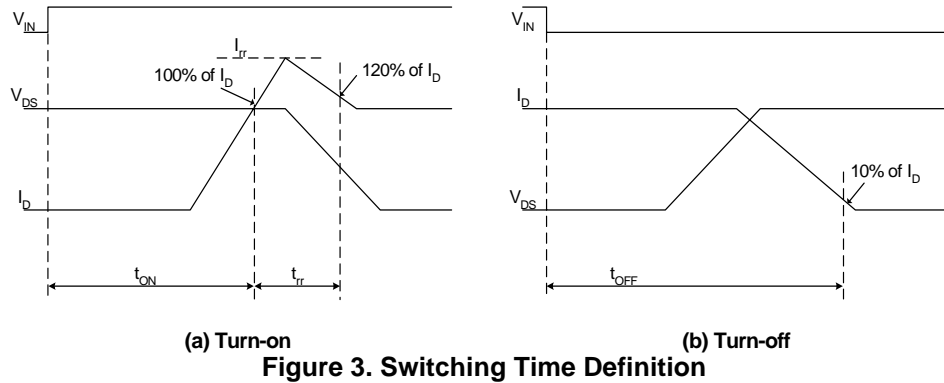


Figure 4. Switching and RBSOA(Single-pulse) Test Circuit (Low-side)

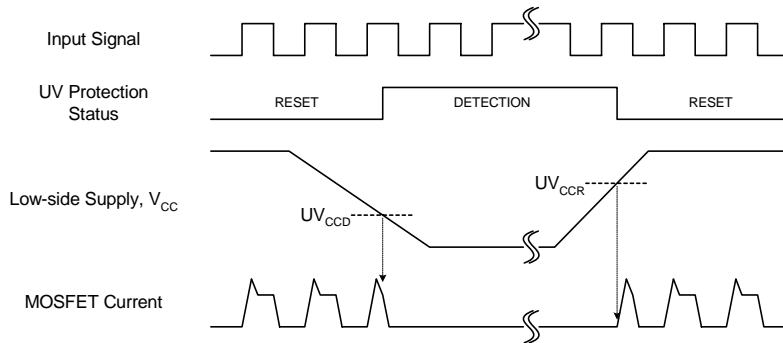


Figure 5. Undervoltage Protection (Low-side)

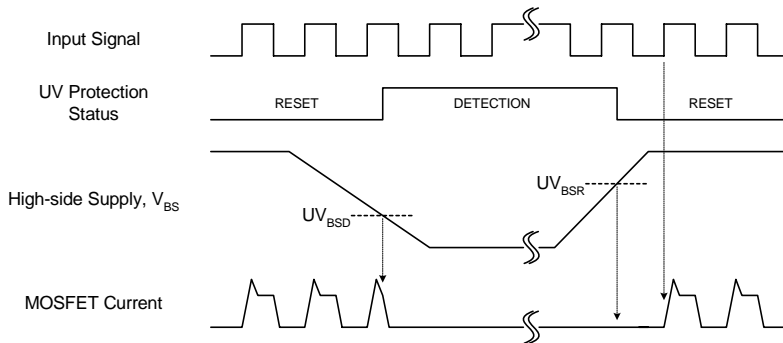


Figure 6. Undervoltage Protection (High-side)

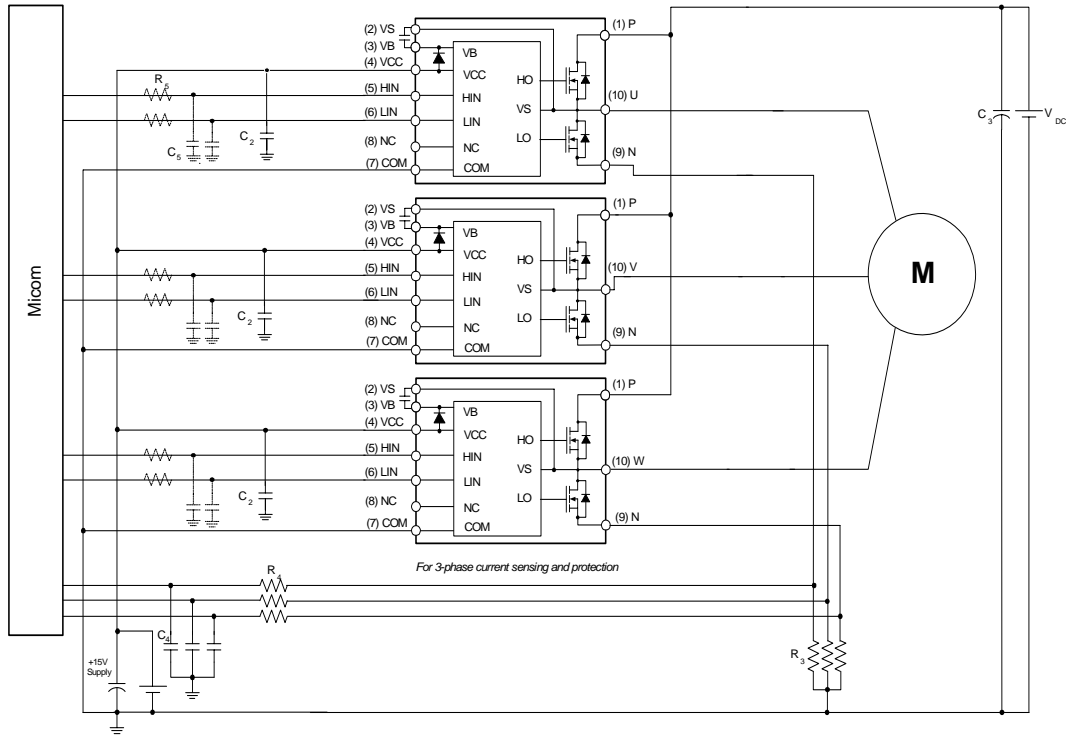
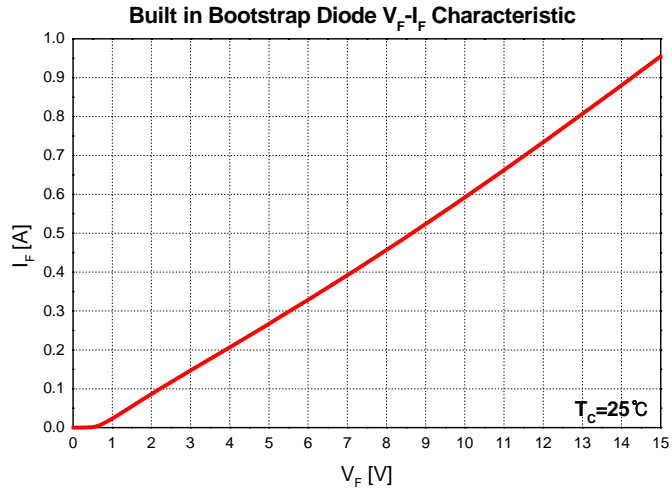


Fig. 7. Example of Application Circuit

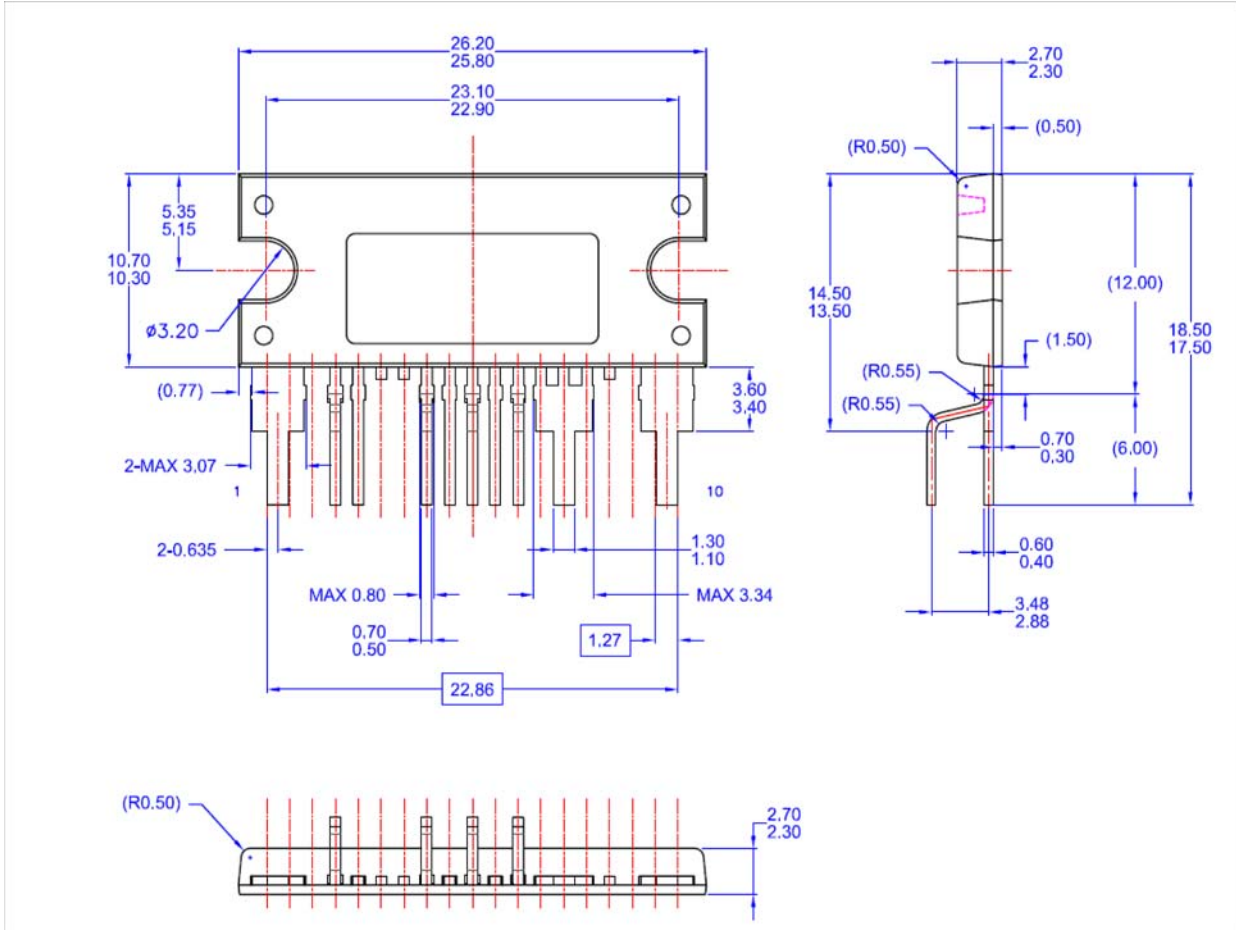


Note:

Built in bootstrap diode includes around 15Ω resistance characteristic.

Figure 8. Built in Bootstrap Diode Characteristics

Detailed Package Outline Drawings





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